

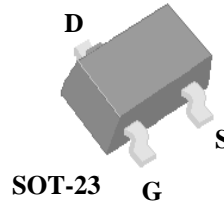
XP2306AGN-HF

Halogen-Free Product

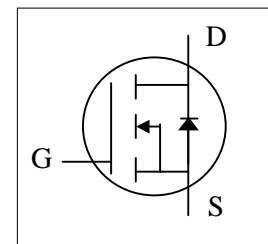


*N-CHANNEL ENHANCEMENT MODE
POWER MOSFET*

- ▼ Capable of 1.8V Gate Drive
- ▼ Lower On-resistance
- ▼ Surface Mount Package
- ▼ RoHS Compliant



| | |
|--------------|--------------|
| BV_{DSS} | 30V |
| $R_{DS(ON)}$ | 35m Ω |
| I_D | 5A |



Description

XSEMI MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-23 package is widely used for all commercial-industrial applications.

Absolute Maximum Ratings @ $T_J=25^\circ\text{C}$ (unless otherwise specified)

| Symbol | Parameter | Rating | Units |
|----------------------------|--|------------|------------------|
| V_{DS} | Drain-Source Voltage | 30 | V |
| V_{GS} | Gate-Source Voltage | +8 | V |
| $I_D@T_A=25^\circ\text{C}$ | Drain Current ³ , V_{GS} @ 4.5V | 5 | A |
| $I_D@T_A=70^\circ\text{C}$ | Drain Current ³ , V_{GS} @ 4.5V | 4 | A |
| I_{DM} | Pulsed Drain Current ¹ | 20 | A |
| $P_D@T_A=25^\circ\text{C}$ | Total Power Dissipation | 1.38 | W |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_J | Operating Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |

Thermal Data

| Symbol | Parameter | Value | Unit |
|--------|--|-------|---------------------------|
| Rthj-a | Maximum Thermal Resistance Junction-ambient ³ | 90 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics @T_j=25°C(unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|---------------------|--|--|------|------|------|-------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =250uA | 30 | - | - | V |
| R _{DS(ON)} | Static Drain-Source On-Resistance ² | V _{GS} =4.5V, I _D =5A | - | - | 35 | mΩ |
| | | V _{GS} =2.5V, I _D =2.6A | - | - | 50 | mΩ |
| | | V _{GS} =1.8V, I _D =1.0A | - | - | 80 | mΩ |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =250uA | 0.3 | - | 1.2 | V |
| g _{fs} | Forward Transconductance | V _{DS} =5V, I _D =5A | - | 9 | - | S |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =24V, V _{GS} =0V | - | - | 10 | uA |
| I _{GSS} | Gate-Source Leakage | V _{GS} = ±8V, V _{DS} =0V | - | - | ±100 | nA |
| Q _g | Total Gate Charge ² | I _D =5A | - | 8.5 | 15 | nC |
| Q _{gs} | Gate-Source Charge | V _{DS} =16V | - | 1 | - | nC |
| Q _{gd} | Gate-Drain ("Miller") Charge | V _{GS} =4.5V | - | 3 | - | nC |
| t _{d(on)} | Turn-on Delay Time ² | V _{DS} =15V | - | 5 | - | ns |
| t _r | Rise Time | I _D =1A | - | 9 | - | ns |
| t _{d(off)} | Turn-off Delay Time | R _G =3.3Ω | - | 20 | - | ns |
| t _f | Fall Time | V _{GS} =5V | - | 5 | - | ns |
| C _{iss} | Input Capacitance | V _{GS} =0V | - | 400 | 1050 | pF |
| C _{oss} | Output Capacitance | V _{DS} =25V | - | 90 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | f=1.0MHz | - | 70 | - | pF |

Source-Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|-----------------|---------------------------------|---|------|------|------|-------|
| V _{SD} | Forward On Voltage ² | I _S =1.2A, V _{GS} =0V | - | - | 1.2 | V |

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 270°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

XSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT

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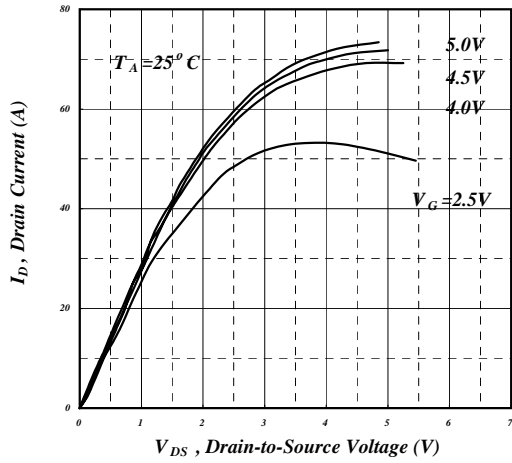


Fig 1. Typical Output Characteristics

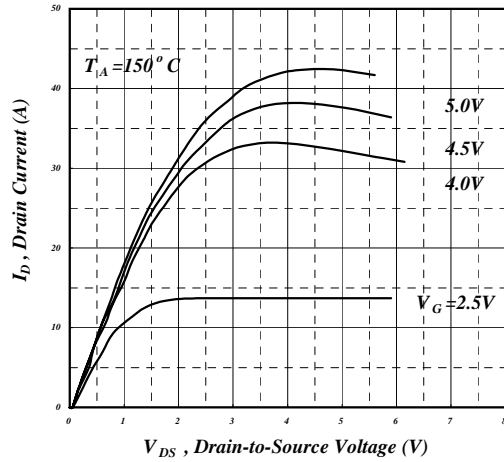


Fig 2. Typical Output Characteristics

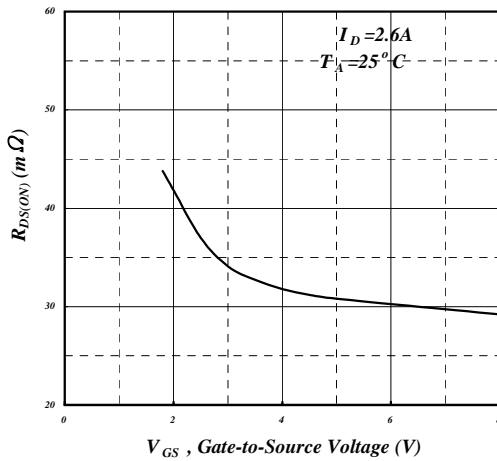


Fig 3. On-Resistance v.s. Gate Voltage

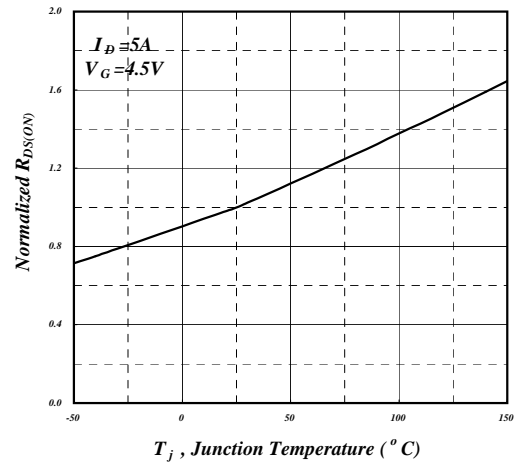


Fig 4. Normalized On-Resistance v.s. Junction Temperature

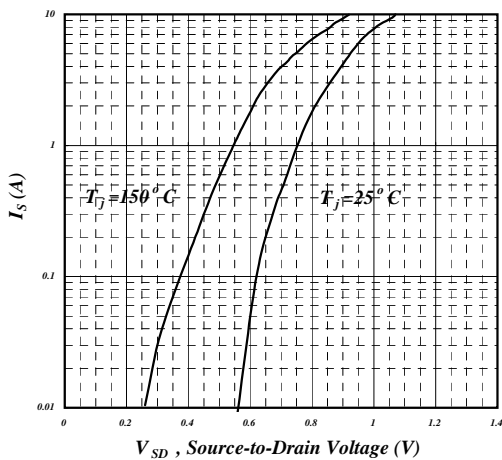


Fig 5. Forward Characteristic of Reverse Diode

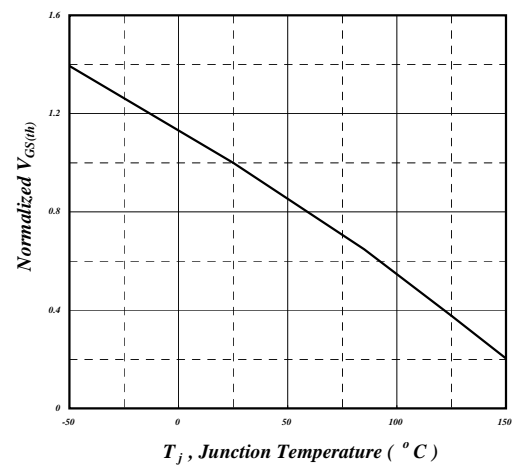


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

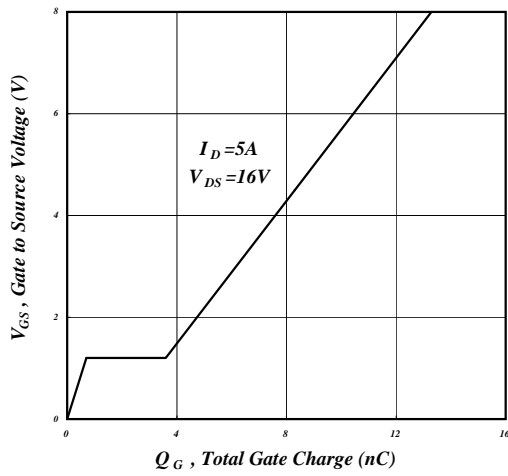


Fig 7. Gate Charge Characteristics

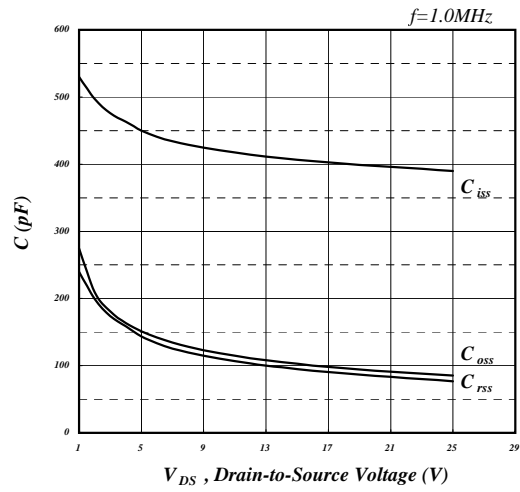


Fig 8. Typical Capacitance Characteristics

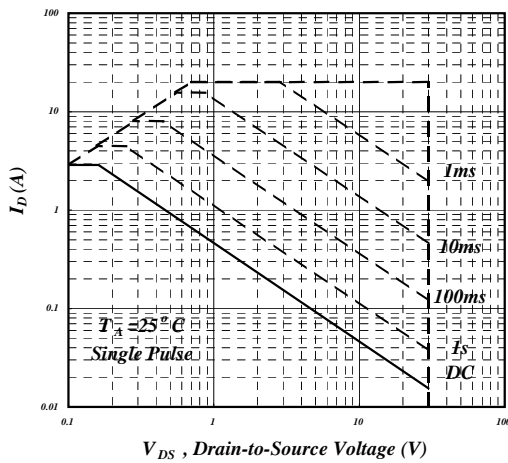


Fig 9. Maximum Safe Operating Area

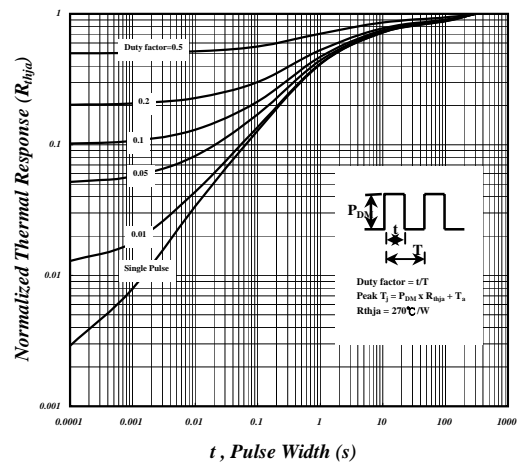


Fig 10. Effective Transient Thermal Impedance

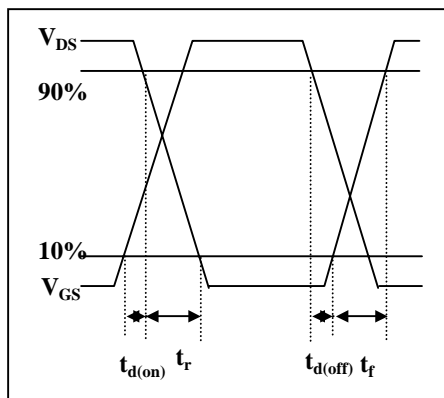


Fig 11. Switching Time Waveform

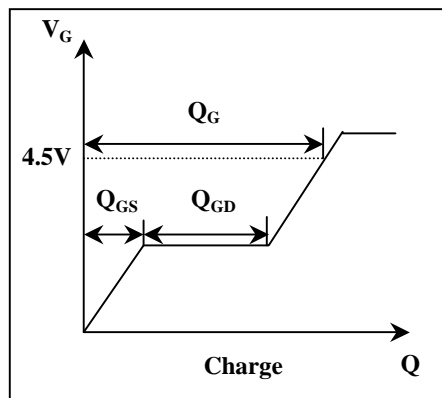


Fig 12. Gate Charge Waveform

MARKING INFORMATION

